



**THE DATASHEET OF
JANSR2N2369AUB**

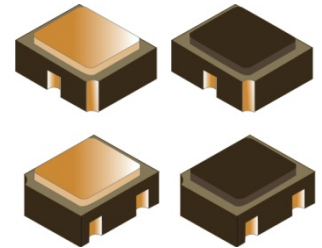


Rad Hard NPN Silicon High Speed Switching Transistor

Screened per MIL-PRF-19500 & ESCC 22900

Screened Levels:
MSR

QPL RANGE and RAD LEVEL	
Radiation Level	MSR2N2369AUB
TID	100 Krad
ELDRS	100 Krad



**UB & UBC
Package**

This RHA level NPN switching transistor 2N2369A device in a UB and UBC package is ideal to drive many high-reliability applications. This device is constructed and screened to a JANSR performance level with radiation test method 1019 wafer lot acceptance conducted on all die lots. Fully compliant to **GSFC EEE-INST-002** reliability, screening and radiation hardness assurance requirements for space flight projects


Important: For the latest information, visit our website <http://www.microsemi.com>.

FEATURES

- JEDEC registered 2N2369
- TID level screened per MIL-PRF-19500
- Also available with ELDRS testing to 0.01 Rad(s)/ sec
- MKCR / MHCR chip die available
- RHA (Radiation hardness assured) lot by lot validation testing via ELDR 0.1 Rad (SI)/sec dose rate

Also available in:

 **AU package**
(surface mount)
MSR2N2369AU

 **TO-206AA package**
(leaded top-hat)
MSR2N2369A

 **UA package**
(surface mount)
MSR2N2369AUA

APPLICATIONS / BENEFITS

- Rad-Hard power supplies
- Rad-Hard motor controls
- General purpose switching
- Instrumentation Amps
- EPS Satellite switching power applications

MAXIMUM RATINGS @ T_A = +25 °C unless otherwise noted

Parameters/Test Conditions	Symbol	Value	Unit
Junction and Storage Temperature	T _J and T _{STG}	-65 to +200	°C
Thermal Resistance Junction-to-Solder Pad	R _{θJSP}	210	°C/W
Thermal Resistance Junction-to-Ambient	R _{θJA}	486	°C/W
Total Power Dissipation:	P _T	0.36	W
@ T _A = +25 °C ⁽¹⁾		0.36	
@ T _C = +125 °C ^{(2) (3)}		0.36	
@ T _{SP} = +125 °C ⁽²⁾		0.36	
Collector-Base Voltage, Emitter Open	V _{CB0}	40	V
Emitter-Base Voltage, Collector Open	V _{EBO}	4.5	V
Collector-Emitter Voltage, Base Open	V _{CEO}	15	V
Collector Current, dc	V _{CES}	40	V
Solder Temperature @ 10 s	T _{SP}	260	°C

- Notes:**
1. Derate linearly 2.06 mW/°C above T_A = +25°C.
 2. Derate linearly 4.8 mW/°C above T_C = +125°C. See [Figure 1](#).
 3. Power dissipation limited to 360 mW per chip regardless of thermal resistance.

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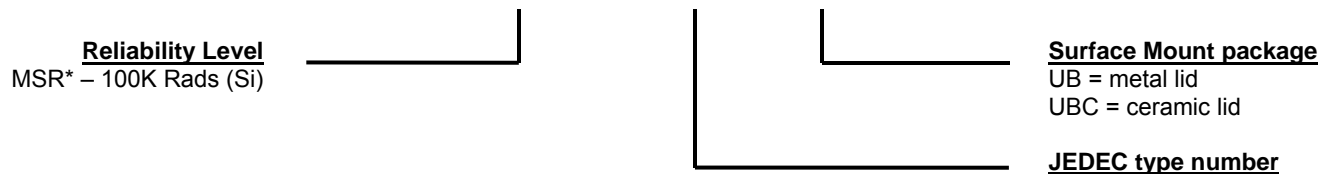
Website:
www.microsemi.com

MECHANICAL and PACKAGING

- CASE: Ceramic with metal lid. UBC is ceramic with ceramic lid.
- TERMINALS: Gold plating over nickel under plate.
- MARKING: Part number, date code, manufacturer's ID.
- TAPE & REEL option: Standard per EIA-418D. Consult factory for quantities.
- WEIGHT: < 0.04 grams
- See [Package Dimensions](#) on last page.

PART NOMENCLATURE

MSR 2N2369A UB



*The MSR designator is our internal part nomenclature assigned to this family of parts, in lieu of pending JANSR submissions through DLA (Defense Logistic Agency).

SYMBOLS & DEFINITIONS

Symbol	Definition
I_B	Base current: The value of the dc current into the base terminal.
I_C	Collector current: The value of the dc current into the collector terminal.
I_E	Emitter current: The value of the dc current into the emitter terminal.
R_G	Gate drive impedance or Gate resistance
V_{CB}	Collector-base voltage: The dc voltage between the collector and the base.
V_{CBO}	Collector-base voltage, base open: The voltage between the collector and base terminals when the emitter terminal is open-circuited.
V_{CE}	Collector-emitter voltage: The dc voltage between the collector and the emitter.
V_{CEO}	Collector-emitter voltage, base open: The voltage between the collector and the emitter terminals when the base terminal is open-circuited.
V_{EB}	Emitter-base voltage: The dc voltage between the emitter and the base
V_{EBO}	Emitter-base voltage, collector open: The voltage between the emitter and base terminals with the collector terminal open-circuited.

ELECTRICAL CHARACTERISTICS @ $T_A = 25\text{ }^\circ\text{C}$ unless otherwise noted.

Parameters / Test Conditions	Symbol	Min.	Max.	Unit
OFF CHARACTERISTICS				
Collector-Emitter Breakdown Voltage $I_C = 10\text{ mA}$	$V_{(BR)CEO}$	15		V
Collector-Base Cutoff Current $V_{CB} = 40\text{ V}$ $V_{CB} = 32\text{ V}$	I_{CBO}		10 0.2	μA
Emitter-Base Cutoff Current $V_{EB} = 4.5\text{ V}$ $V_{EB} = 4.0\text{ V}$	I_{EBO}		10 0.25	μA
Collector-Emitter Cutoff Current $V_{CE} = 20\text{ V}$	I_{CES}		0.4	μA
ON CHARACTERISTICS ⁽¹⁾				
Forward-Current Transfer Ratio $I_C = 10\text{ mA}, V_{CE} = 0.35\text{ V}$ $I_C = 30\text{ mA}, V_{CE} = 0.4\text{ V}$ $I_C = 10\text{ mA}, V_{CE} = 1.0\text{ V}$ $I_C = 100\text{ mA}, V_{CE} = 1.0\text{ V}$	h_{FE}	40 30 40 20	120 120 120 120	
Collector-Emitter Saturation Voltage $I_C = 10\text{ mA}, I_B = 1.0\text{ mA}$ $I_C = 30\text{ mA}, I_B = 3.0\text{ mA}$	$V_{CE(sat)}$		0.2 0.25	V
Base-Emitter Voltage $I_C = 10\text{ mA}, I_B = 1.0\text{ mA}$ $I_C = 30\text{ mA}, I_B = 3.0\text{ mA}$	$V_{BE(sat)}$	0.7	0.85 0.90	V

DYNAMIC CHARACTERISTICS

Parameters / Test Conditions	Symbol	Min.	Max.	Unit
Small-Signal Short-Circuit Forward Current Transfer Ratio $I_C = 10\text{ mA}, V_{CE} = 1.0\text{ V}, f = 1.0\text{ kHz}$	h_{fe}	20		
Magnitude of Small-Signal Short-Circuit Forward Current Transfer Ratio $I_C = 10\text{ mA}, V_{CE} = 10\text{ V}, f = 100\text{ MHz}$	$ h_{fe} $	5.0	10	
Output Capacitance $V_{CB} = 5\text{ V}, I_E = 0, 100\text{ kHz} \leq f \leq 1.0\text{ MHz}$	C_{obo}		4.0	pF
Input Capacitance $V_{EB} = 0.5\text{ V}, I_C = 0, 100\text{ kHz} \leq f \leq 1.0\text{ MHz}$	C_{ibo}		5.0	pF

(1) Pulse Test: Pulse Width = 300 μs , Duty Cycle $\leq 2.0\%$

SWITCHING CHARACTERISTICS

Parameters / Test Conditions	Symbol	Min.	Max.	Unit
Turn-On Time $I_C = 10\text{ mA}, I_{B1} = 3.0\text{ mA}, I_{B2} = -1.5\text{ mA}$	t_{on}		12	ns
Turn-Off Time $I_C = 10\text{ mA}, I_{B1} = 3.0\text{ mA}, I_{B2} = -1.5\text{ mA}$	t_{off}		18	ns

GRAPHS

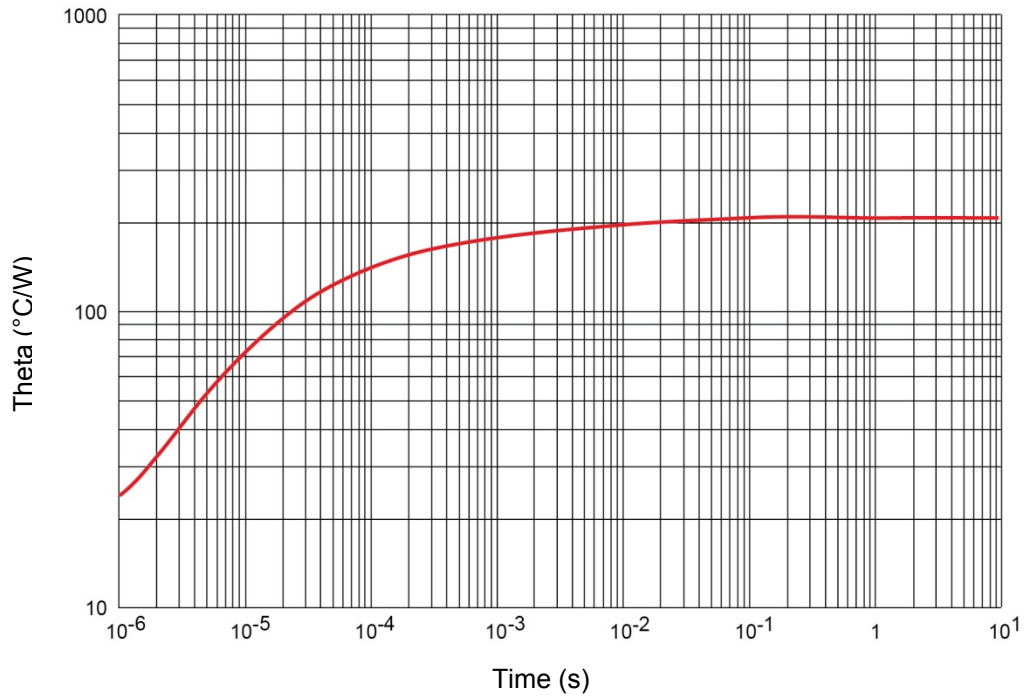


FIGURE 1
Thermal Impedance Graph ($R_{\theta JSF}$)

Radiation hardness assurance

The MSR series product are guaranteed in radiation with full compliance to MIL-PRF-19500 specification JANSR level and are also guaranteed to meet ESCC 22900 specifications (General specifications).

Radiation assurance MIL-PRF-19500

MSR parts are guaranteed at 100 krad (Si), tested, in full compliancy with the MIL-PRF-19500 specification, specifically the Group D, subgroup 2 inspection, between 50 and 300 rad/s. All test are performed in accordance to MIL-PRF-19500 and test method 1019 of MIL-STD-750 for total Ionizing dose.

- Each wafer of each lot is tested, (note 1). The table below provides for each monitored parameters of the test conditions and the acceptance criteria

Radiation summary

Radiation test (Note 1)	100 krad ESCC
Wafer test	each
Part tested	10 biased + 10 unbiased
Dose rate	0.1 rad/s
Acceptance	MIL-STD-750 method 1019
Displacement damage	Optional

1. Microsemi MSR products will exceed required testing of ESCC basic specification 22900
- 2.

ELECTRICAL CHARACTERISTICS @ T_A = +25 °C, unless otherwise noted (continued)

POST RADIATION

Parameters / Test Conditions	Symbol	Min.	Max.	Unit
Collector to Base Cutoff Current V _{CB} = 40 V V _{CB} = 32 V	I _{CBO}		20 0.4	μA
Emitter to Base Cutoff Current V _{EB} = 4.5 V V _{EB} = 4 V	I _{EBO}		20 0.50	μA
Collector to Emitter Breakdown Voltage I _C = 10 mA	V _{(BR)CEO}	15		V
Forward-Current Transfer Ratio ⁽²⁾ I _C = 10 mA, V _{CE} = 0.35 V I _C = 30 mA, V _{CE} = 0.4 V I _C = 10 mA, V _{CE} = 1.0 V I _C = 100 mA, V _{CE} = 1.0 V	[h _{FE}]	[20] [15] [20] [10]	120 120 120 120	
Collector-Emitter Saturation Voltage I _C = 10 mA, I _B = 1.0 mA I _C = 30 mA, I _B = 3.0 mA	V _{CE(sat)}		0.23 0.29	V
Base-Emitter Saturation Voltage I _C = 10 mA, I _B = 1.0 mA I _C = 30 mA, I _B = 3.0 mA	V _{BE(sat)}	0.70	0.98 1.04	V

- (2) See method 1019 of MIL-STD-750 for how to determine [h_{FE}] by first calculating the delta (1/h_{FE}) from the pre- and post-radiation h_{FE}. Notice the [h_{FE}] is not the same as h_{FE} and cannot be measured directly. The [h_{FE}] value can never exceed the pre-radiation minimum h_{FE} that it is based upon.

ESCC radiation assurance

Each product lot is tested according to the ESCC basic specification 22900, with a minimum of 21 samples per diffusion lot and 10 samples per wafer, one sample being kept as un-irradiated sample, all of them being fully compliant with the applicable ESCC generic and/or detailed specification.

- Test of 10 pieces by wafer, 10 biased at least 80% of $V_{(BR)CEO}$, 10 unbiased and 1 kept for reference
- Irradiation at 0.1 rad (Si)/s
- Acceptance criteria of each individual wafer if as 100 krad guaranteed if all 20 samples comply with the post radiation electrical characteristics provided in [Table 4](#) (post radiation electrical characteristics for the 2N2369A)
- Delivery together with the parts of the radiation verification test (RVT) report of the particular wafer used to manufacture the products. This RVT includes the value of each parameter at 30, 50, 70 and 100 krad (Si) and after 24 hour annealing at room temperature and after an additional 168 hour annealing at 100°C.

Radiation summary

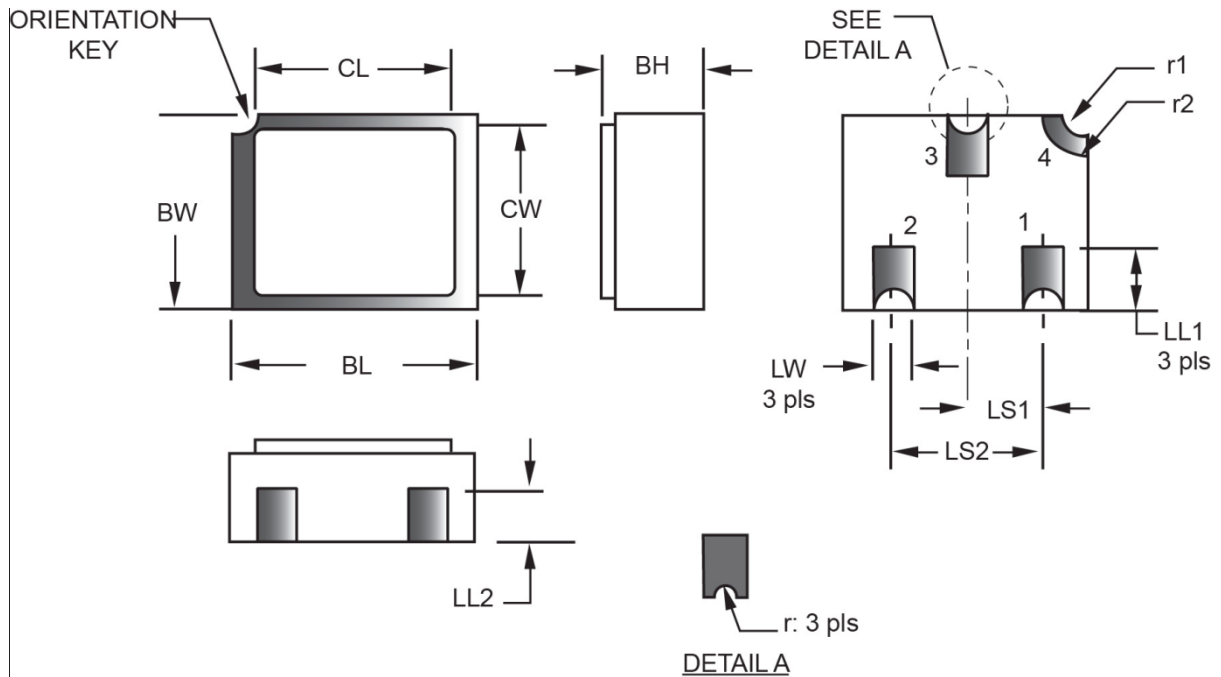
Radiation test (Note 1)	100 krad ESCC
Wafer test	each
Part	10 biased + 10 unbiased
Dose rate	0.1 rad/s
Acceptance	MIL-STD-750 method 1019
Displacement damage	Optional

1. Microsemi MSR products will exceed required testing of *ESCC basic specification 22900*

POST RADIATION- Table 4

Parameters / Test Conditions	Symbol	Min.	Max.	Unit
Collector to Base Cutoff Current $V_{CB} = 40\text{ V}$ $V_{CB} = 32\text{ V}$	I_{CBO}		20 0.4	μA
Emitter to Base Cutoff Current $V_{EB} = 4.5\text{ V}$ $V_{EB} = 4\text{ V}$	I_{EBO}		20 0.50	μA
Collector to Emitter Breakdown Voltage $I_C = 10\text{ mA}$	$V_{(BR)CEO}$	15		V
Forward-Current Transfer Ratio ⁽²⁾ $I_C = 10\text{ mA}, V_{CE} = 0.35\text{ V}$ $I_C = 30\text{ mA}, V_{CE} = 0.4\text{ V}$ $I_C = 10\text{ mA}, V_{CE} = 1.0\text{ V}$ $I_C = 100\text{ mA}, V_{CE} = 1.0\text{ V}$	$[h_{FE}]$	[20] [15] [20] [10]	120 120 120 120	
Collector-Emitter Saturation Voltage $I_C = 10\text{ mA}, I_B = 1.0\text{ mA}$ $I_C = 30\text{ mA}, I_B = 3.0\text{ mA}$	$V_{CE(sat)}$		0.23 0.29	V
Base-Emitter Saturation Voltage $I_C = 10\text{ mA}, I_B = 1.0\text{ mA}$ $I_C = 30\text{ mA}, I_B = 3.0\text{ mA}$	$V_{BE(sat)}$	0.70	0.98 1.04	V

1. This value is determined from $\Delta(1/h_{fe})$ using pre & post radiation values of h_{fe} . $[h_{fe}]$ should not exceed the pre- radiation minimum h_{fe} .

PACKAGE DIMENSIONS


Symbol	Dimensions				Note	Symbol	Dimensions				Note
	inch		millimeters				inch		millimeters		
	Min	Max	Min	Max			Min	Max	Min	Max	
BH	0.046	0.056	1.17	1.42		LS1	0.035	0.039	0.89	0.99	
BL	0.115	0.128	2.92	3.25		LS2	0.071	0.079	1.80	2.01	
BW	0.095	0.108	2.41	2.74		LW	0.016	0.024	0.41	0.61	
CL	-	0.128	-	3.25		r	-	0.008	-	0.20	
CW	-	0.108	-	2.74		r1	-	0.012	-	0.31	
LL1	0.022	0.038	0.56	0.97		r2	-	0.022	-	0.056	
LL2	0.014	0.035	0.36	0.89							

NOTES:

1. Dimensions are in inches. Millimeters are given for information only.
2. Ceramic package only.
3. Hatched areas on package denote metallized areas.
4. Pad 1 = Base, Pad 2 = Emitter, Pad 3 = Collector, Pad 4 = Shielding not connected to ceramic lid.
5. In accordance with ASME Y14.5M, diameters are equivalent to Φ x symbology.

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